

09/254521

PCT/GB97/02388

WO 98/11425

Figure 1. PL image of as-grown defects in CZ Si

Scan area 1mm x 1mm

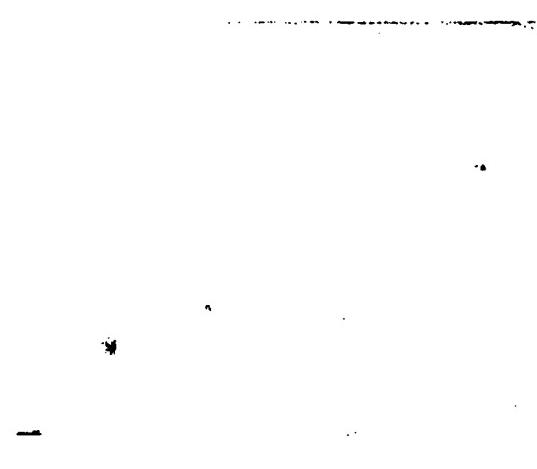


Figure 2. PL image of as-grown defects in CZ Si after Fe contamination 1×10^{11} atoms.cm⁻³

Scan area 1mm x 1mm



Figure 3. PL image of oxygen precipitates in annealed Si

Scan area 1mm x 1mm

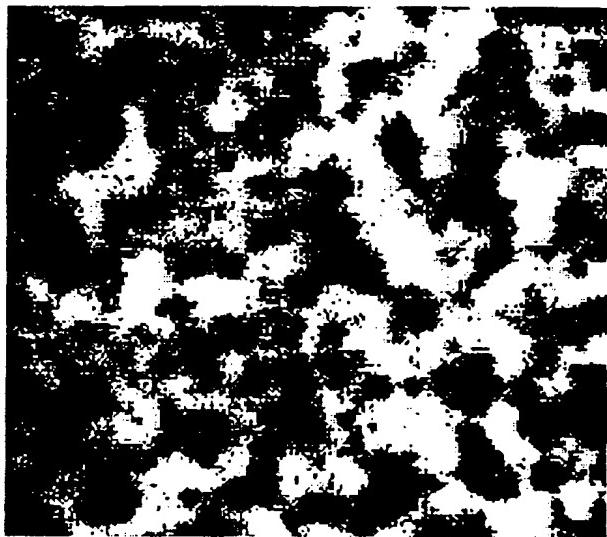


Figure 4. PL image of Ni silicide precipitates in CMOS processed test wafer

Scan area 500 x 500 μm



Figure 5. PL image of Cu silicide precipitates in CMOS processed test wafer

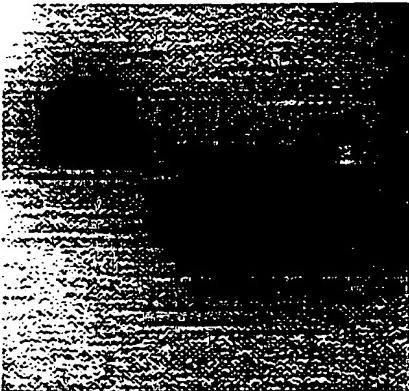
Scan area 100 x 100 μm



Figure 6. PL image of Cu silicide precipitates in CMOS processed test wafer, a) high injection, b) low injection.

Scan area 37 x 39 μm

a)



b)

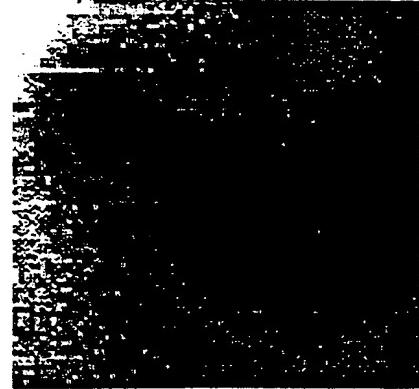


Figure 7. Micrograph of LOCOS test structure

Scan area 120 x 60 μm

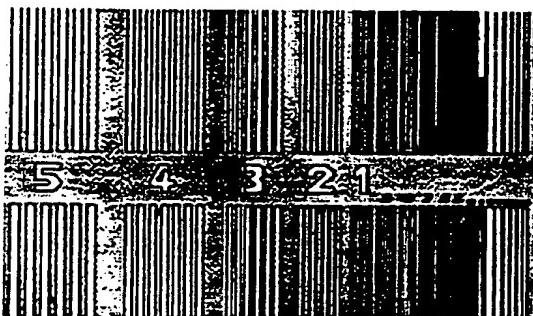


Figure 8. PL image of LOCOS test structure revealing a high density of dislocations

Scan area 120 x 60 μm



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Figure 9

